



PJT7603

Complementary Enhancement Mode MOSFET – ESD Protected

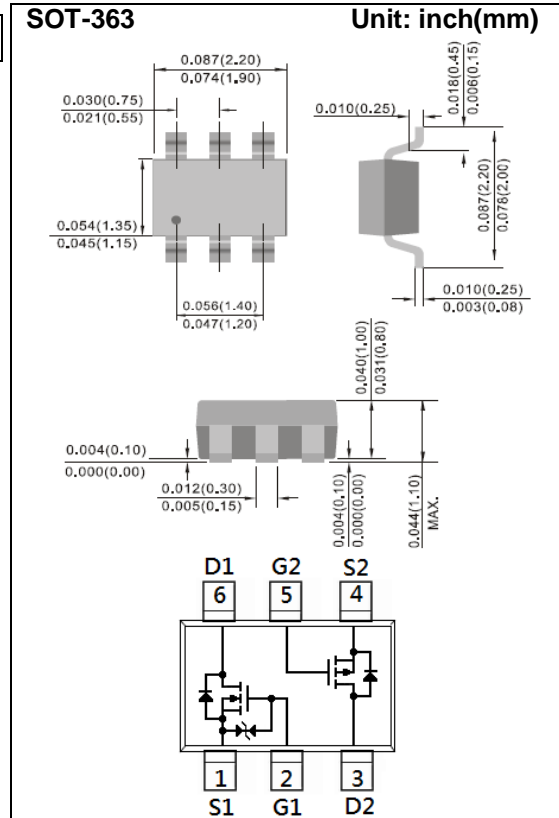
Voltage 50 / -60V **Current** 0.4A / -0.25A

Features

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case: SOT-363 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0002 ounces, 0.006 grams
- Marking: T63



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage	V _{DS}	50	-60	V	
Gate-Source Voltage	V _{GS}	+20	+20	V	
Continuous Drain Current	I _D	400	-250	mA	
Pulsed Drain Current (Note 4)	I _{DM}	1200	-900	mA	
Power Dissipation	P _D	T _a =25°C		350	mW
		Derate above 25°C		2.8	mW/°C
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55~150		°C	
Typical Thermal resistance	R _{θJA}			°C/W	
- Junction to Ambient (Note 3)		357			



PJT7603

N-Channel Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	50	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.9	1.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=500mA$	-	1.2	1.5	Ω
		$V_{GS}=4.5V, I_D=200mA$	-	1.3	2.5	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=50V, V_{GS}=0V$	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 10	μA
Dynamic (Note 5)						
Total Gate Charge	Q_g	$V_{DS}=25V, I_D=500mA,$ $V_{GS}=4.5V$	-	0.95	-	nC
Gate-Source Charge	Q_{gs}		-	0.34	-	
Gate-Drain Charge	Q_{gd}		-	0.32	-	
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$	-	36	-	μF
Output Capacitance	C_{oss}		-	11	-	
Reverse Transfer Capacitance	C_{rss}		-	6.6	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=25V, I_D=500mA,$ $V_{GS}=10V,$ $R_G=6\Omega$ (Note 1,2)	-	2.3	-	ns
Turn-On Rise Time	t_r		-	20	-	
Turn-Off Delay Time	$t_{d(off)}$		-	7	-	
Turn-Off Fall Time	t_f		-	20	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	400	mA
Diode Forward Voltage	V_{SD}	$I_S=500mA, V_{GS}=0V$	-	0.9	1.5	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
4. The maximum current rating is package limited.
5. Guaranteed by design, not subject to production testing.



PJT7603

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PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-60	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1.0	-1.5	-2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-500mA	-	2.4	4	Ω
		V _{GS} =-4.5V, I _D =-200mA	-	2.7	6	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-48V, V _{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Dynamic (Note 5)						
Total Gate Charge	Q _g	V _{DS} =-25V, I _D =-100mA, V _{GS} =-4.5V	-	1.1	-	nC
Gate-Source Charge	Q _{gs}		-	0.3	-	
Gate-Drain Charge	Q _{gd}		-	0.2	-	
Input Capacitance	C _{iss}	V _{DS} =-25V, V _{GS} =0V, f=1.0MHZ	-	51	-	pF
Output Capacitance	C _{oss}		-	15	-	
Reverse Transfer Capacitance	C _{rss}		-	2.2	-	
Turn-On Delay Time	td _(on)	V _{DD} =-25V, I _D =-100mA, V _{GS} =-10V, R _G =6Ω (Note 1,2)	-	4.8	-	ns
Turn-On Rise Time	tr		-	19	-	
Turn-Off Delay Time	td _(off)		-	52	-	
Turn-Off Fall Time	tf		-	32	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	-250	mA
Diode Forward Voltage	V _{SD}	I _S =-500mA, V _{GS} =0V	-	-0.9	-1.5	V



PJT7603

N-Channel TYPICAL CHARACTERISTIC CURVES

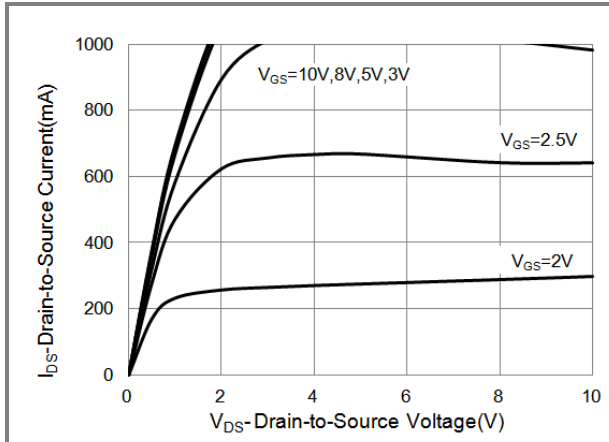


Fig.1 On-Region Characteristics

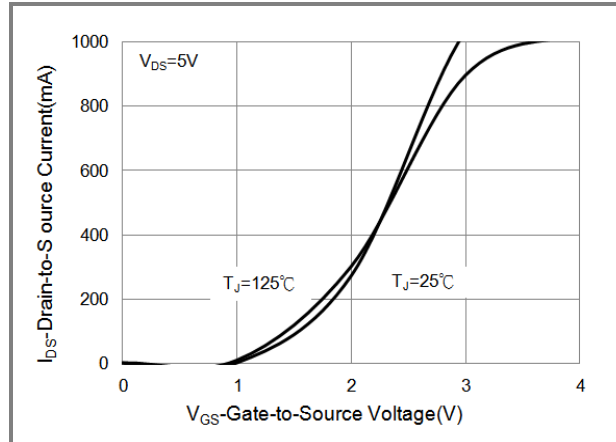


Fig.2 Transfer Characteristics

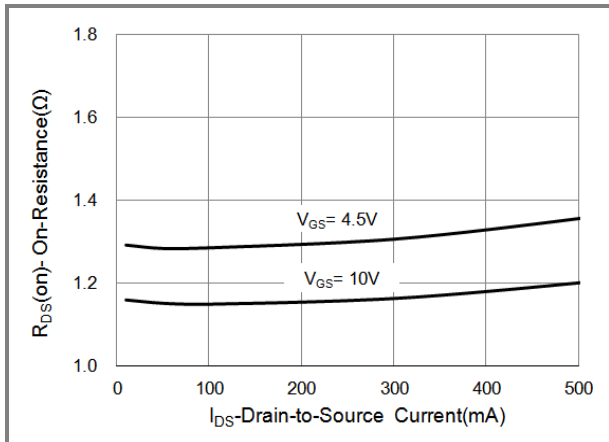


Fig.3 On-Resistance vs. Drain Current

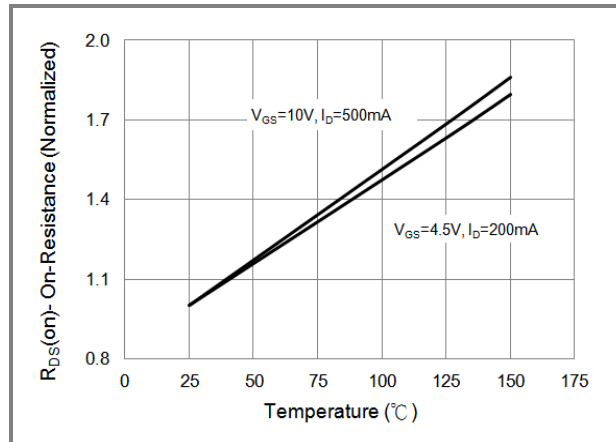


Fig.4 On-Resistance vs. Junction temperature

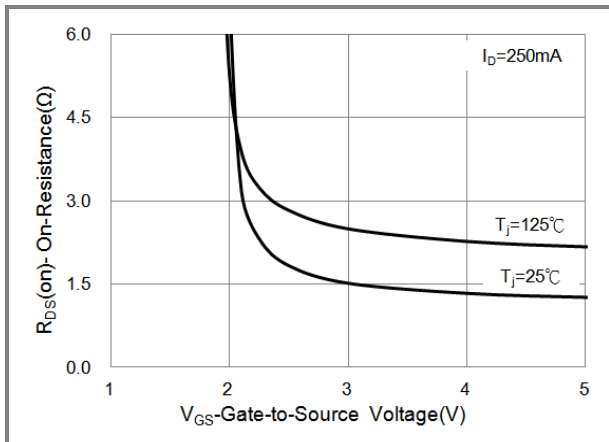


Fig.5 On-Resistance Variation with VGS.

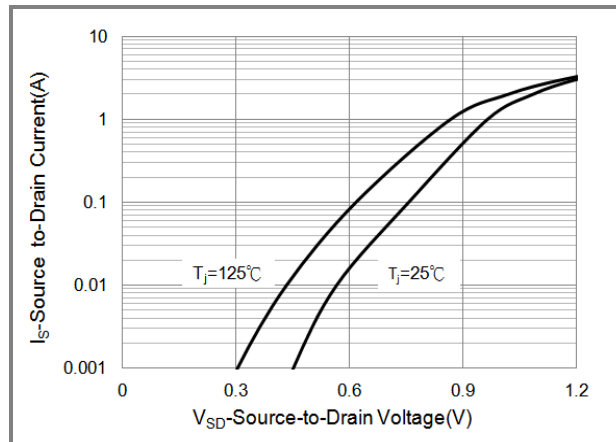


Fig.6 Body Diode Characteristics



PJT7603

N-Channel TYPICAL CHARACTERISTIC CURVES

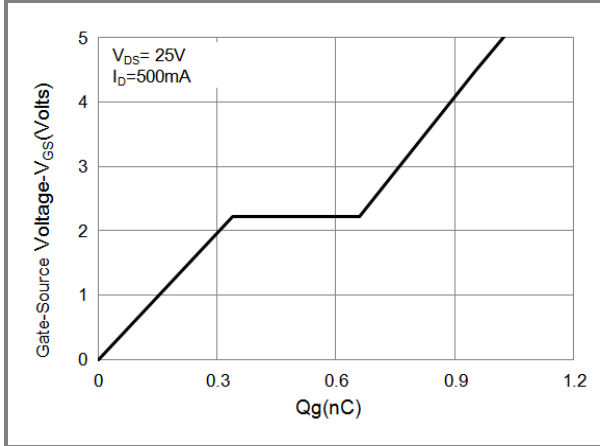


Fig.7 Gate-Charge Characteristics

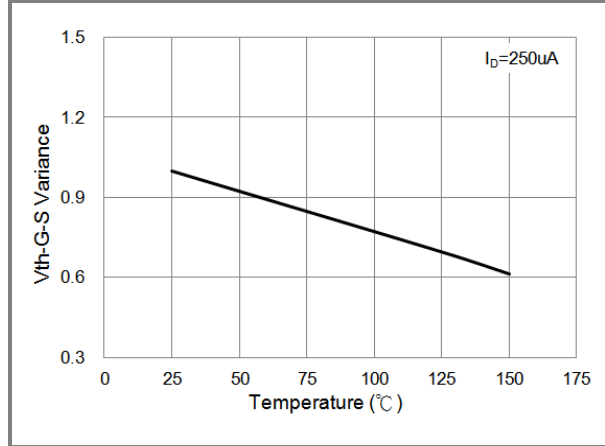


Fig.8 Threshold Voltage Variation with Temperature.

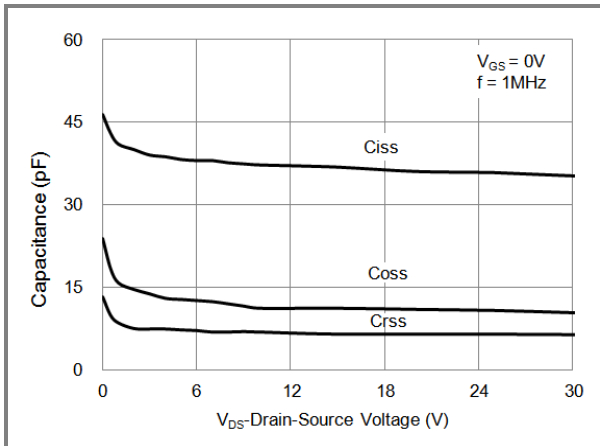


Fig.9 Capacitance vs. Drain-Source Voltage.



PJT7603

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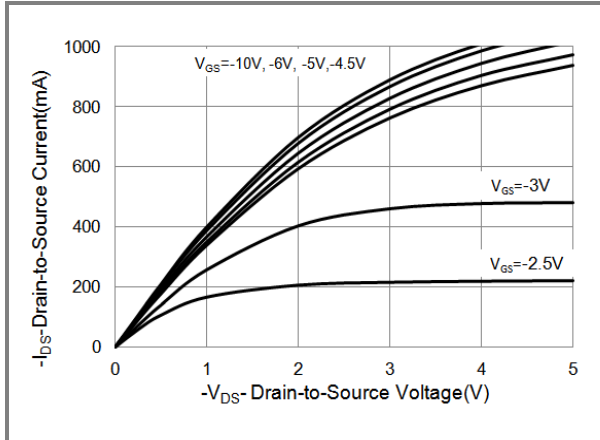


Fig.1 On-Region Characteristics

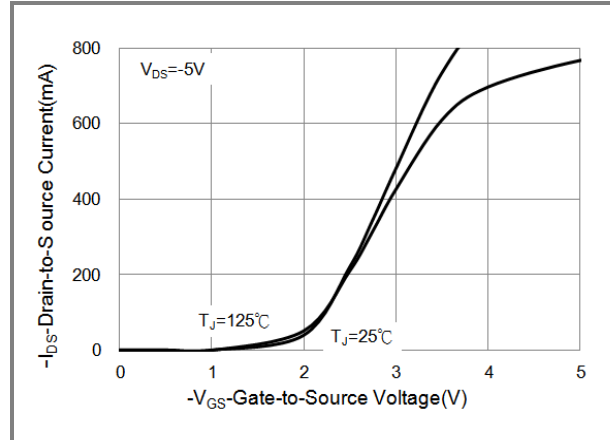


Fig.2 Transfer Characteristics

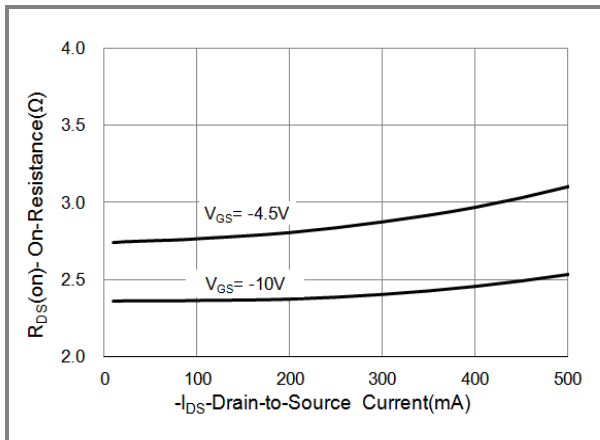


Fig.3 On-Resistance vs. Drain Current

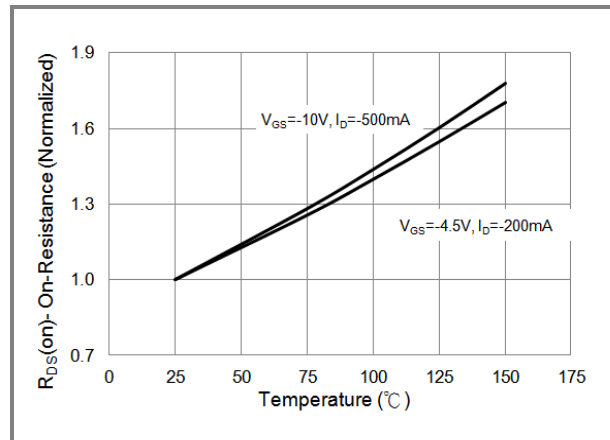


Fig.4 On-Resistance vs. Junction temperature

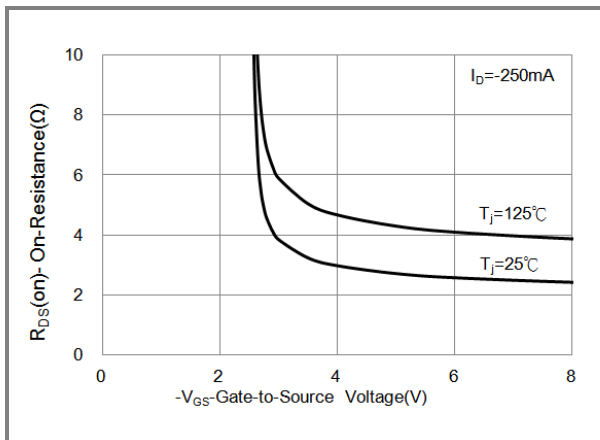


Fig.5 On-Resistance Variation with V_{G_S} .

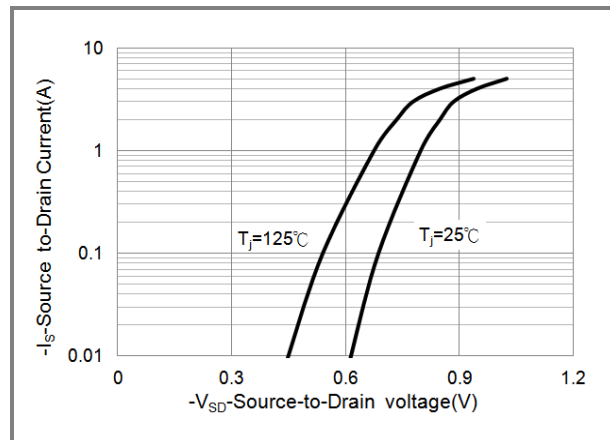


Fig.6 Body Diode Characteristics



PJT7603

P-Channel TYPICAL CHARACTERISTIC CURVES

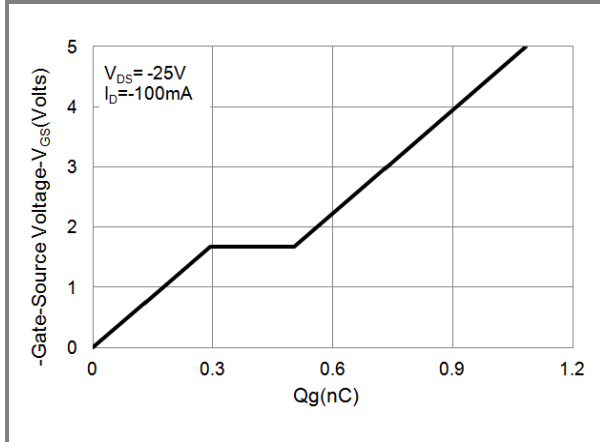


Fig.7 Gate-Charge Characteristics

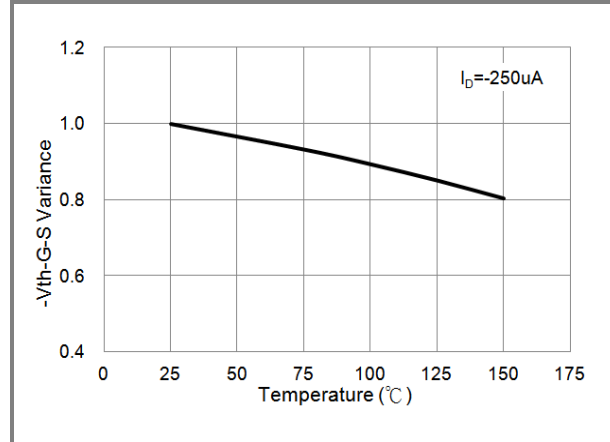


Fig.8 Threshold Voltage Variation with Temperature.

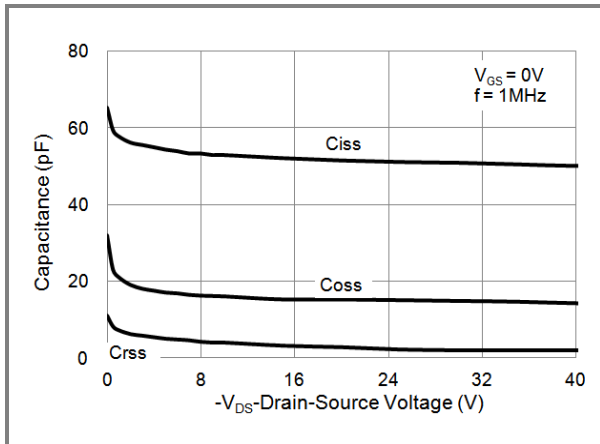


Fig.9 Threshold Voltage Variation with Temperature.

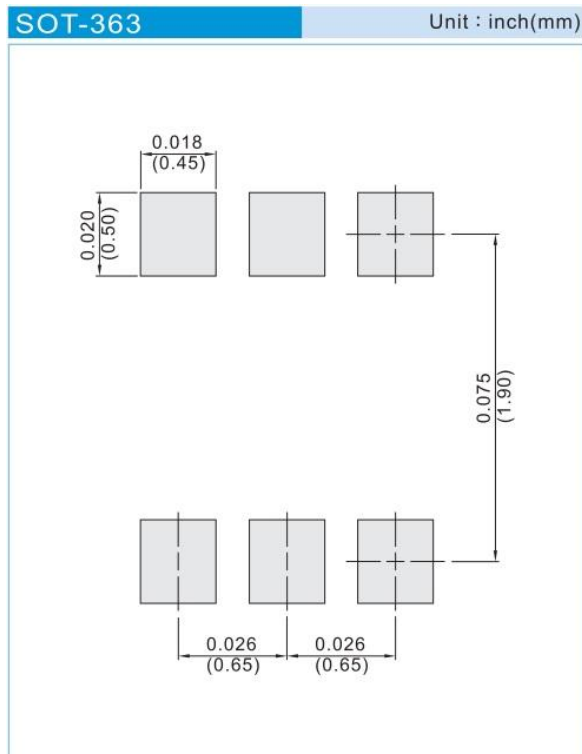


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PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJT7603_R1_00001	SOT-363	3K pcs / 7" reel	T63	Halogen free
PJT7603_R2_00001	SOT-363	10K pcs / 13" reel	T63	Halogen free

MOUNTING PAD LAYOUT





PJT7603

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